

Approval Sheet

Customer	
Product Number	M3SW-2GSJCCN9-Q
Module speed	PC3-10600
Pin	204 pin
CI-tRCD-tRP	9-9-9
DRAM Operating Temp	0°C~85°C
Date	10 th March 2014

Approval by Customer

P/N:

Signature:

Date:

Sales: _____ Sr. Technical Manager: John Hsieh

Rev 1.0

1. Features

Key Parameter

Industry Nomenclature	Speed Grade	Data Rate MT/s			tAA (ns)	tRCD (ns)	tRP (ns)	tRC (ns)
		CL=7	CL=9	CL=11				
PC3-10600	N	1066	1333	1333	13.5	13.5	13.5	49.5

- JEDEC Standard 204-pin Dual In-Line Memory Module
- Intend for PC3-10600 applications
- Inputs and Outputs are SSTL-15 compatible
- VDD=VDDQ= 1.5 Volt \pm 0.075
- Bi-directional Differential Data Strobe
- DLL aligns DQ and DQS transition with CK transition
- SDRAMs have 8 internal banks for concurrent operation
- Normal and Dynamic On-Die Termination support.
- SDRAMs are 78-ball BGA Package
- 8 bit pre-fetch
- Two different termination values (Rtt_Nom & Rtt_WR)
- Auto & self refresh 7.8 μ s ($T_A \leq +85^\circ\text{C}$)
- 15/10/1 Addressing (row/column/rank)-2GB
- DRAM operating temperature range $0^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$
- Programmable Device Operation:
 - Burst Type: Sequential or Interleave
 - Device CAS# Latency: 9
 - Burst Length: switch on-the-fly: BL=8 or BC 4
- RoHS Compliant (*Section 14*)

2. Environmental Requirements

iDIMM are intended for use in standard office environments that have limited capacity for heating and air conditioning.

Symbol	Parameter	Rating	Units	Notes
TOPR	Operating Temperature (ambient)	0 to +65	°C	1
TSTG	Storage Temperature	-50 to +100	°C	
HOPR	Operating Humidity (relative)	10 to 90	%	
HSTG	Storage Humidity (without condensation)	5 to 95	%	
PBAR	Barometric Pressure (operating & storage)	105 to 69	K Pascal	1,2

1. The component maximum case temperature (Tcase) shall not exceed the value specified in the DDR DRAM component specification.
 2. Up to 9850 ft.

3. DRAM Parameters by device density

RTT_Nom Setting	Parameter	2Gb	Units
tRFC	REF command ACT or REF command time	160	ns
tREFI	Average periodic refresh interval	0°C ≤ TCASE ≤ 85°C	7.8 μs
		85°C ≤ TCASE ≤ 95°C	3.9 μs

4. Ordering Information

DDR3 SODIMM						
Part Number	Density	Speed	Organization	Number of DRAM	Number of rank	ECC
M3SW-2GSJCCN9-Q	2GB	PC3-10600	256Mx64	8	1	N

5. Pin Configurations (Front side/Back side)

X64 SODIMM

Pin	Front	Pin	Back	Pin	Front	Pin	Back	Pin	Front	Pin	Back
1	VREFDQ	2	V _{SS}	69	DQ27	70	DQ31	137	DQS4	138	V _{SS}
3	V _{SS}	4	DQ4	71	V _{SS}	72	V _{SS}	139	V _{SS}	140	DQ38
5	DQ0	6	DQ5	73	CKE0	74	CKE1	141	DQ34	142	DQ39
7	DQ1	8	V _{SS}	75	V _{DD}	76	V _{DD}	143	DQ35	144	V _{SS}
9	V _{SS}	10	/DQS0	77	NC	78	A15 ***	145	V _{SS}	146	DQ44
11	DM0	12	DQS0	79	BA2	80	A14 ***	147	DQ40	148	DQ45
13	V _{SS}	14	V _{SS}	81	V _{DD}	82	V _{DD}	149	DQ41	150	V _{SS}
15	DQ2	16	DQ6	83	A12, /BC	84	A11	151	V _{SS}	152	/DQS5
17	DQ3	18	DQ7	85	A9	86	A7	153	DM5	154	DQS5
19	V _{SS}	20	V _{SS}	87	V _{DD}	88	V _{DD}	155	V _{SS}	156	V _{SS}
21	DQ8	22	DQ12	89	A8	90	A6	157	DQ42	158	DQ46
23	DQ9	24	DQ13	91	A5	92	A4	159	DQ43	160	DQ47
25	V _{SS}	26	V _{SS}	93	V _{DD}	94	V _{DD}	161	V _{SS}	162	V _{SS}
27	/DQS1	28	DM1	95	A3	96	A2	163	DQ48	164	DQ52
29	DQS1	30	/Reset	97	A1	98	A0	165	DQ49	166	DQ53
31	V _{SS}	32	V _{SS}	99	V _{DD}	100	V _{DD}	167	V _{SS}	168	V _{SS}
33	DQ10	34	DQ14	101	CK0	102	CK1	169	/DQS6	170	DM6
35	DQ11	36	DQ15	103	/CK0	104	/CK1	171	DQS6	172	V _{SS}
37	V _{SS}	38	V _{SS}	105	V _{DD}	106	V _{DD}	173	V _{SS}	174	DQ54
39	DQ16	40	DQ20	107	A10, /AP	108	BA1	175	DQ50	176	DQ55
41	DQ17	42	DQ21	109	BA0	110	/RAS	177	DQ51	178	V _{SS}
43	V _{SS}	44	V _{SS}	111	V _{DD}	112	V _{DD}	179	V _{SS}	180	DQ60
45	/DQS2	46	DM2	113	/WE	114	/S0	181	DQ56	182	DQ61
47	DQS2	48	V _{SS}	115	/CAS	116	ODT0	183	DQ57	184	V _{SS}
49	V _{SS}	50	DQ22	117	V _{DD}	118	V _{DD}	185	V _{SS}	186	/DQS7
51	DQ18	52	DQ23	119	A13 ***	120	ODT1	187	DM7	188	DQS7
53	DQ19	54	V _{SS}	121	/S1	122	NC *	189	V _{SS}	190	V _{SS}
55	V _{SS}	56	DQ28	123	V _{DD}	124	V _{DD}	191	DQ58	192	DQ62
57	DQ24	58	DQ29	125	TEST/NC	126	VREFCA	193	DQ59	194	DQ63
59	DQ25	60	V _{SS}	127	V _{SS}	128	V _{SS}	195	V _{SS}	196	V _{SS}
61	V _{SS}	62	/DQS3	129	DQ32	130	DQ36	197	SA0	198	/EVENT
63	DM3	64	DQS3	131	DQ33	132	DQ37	199	VDDSPD	200	SDA
65	V _{SS}	66	V _{SS}	133	V _{SS}	134	V _{SS}	201	SA1	202	SCL
67	DQ26	68	DQ30	135	/DQS4	136	DM4	203	Vtt	204	Vtt

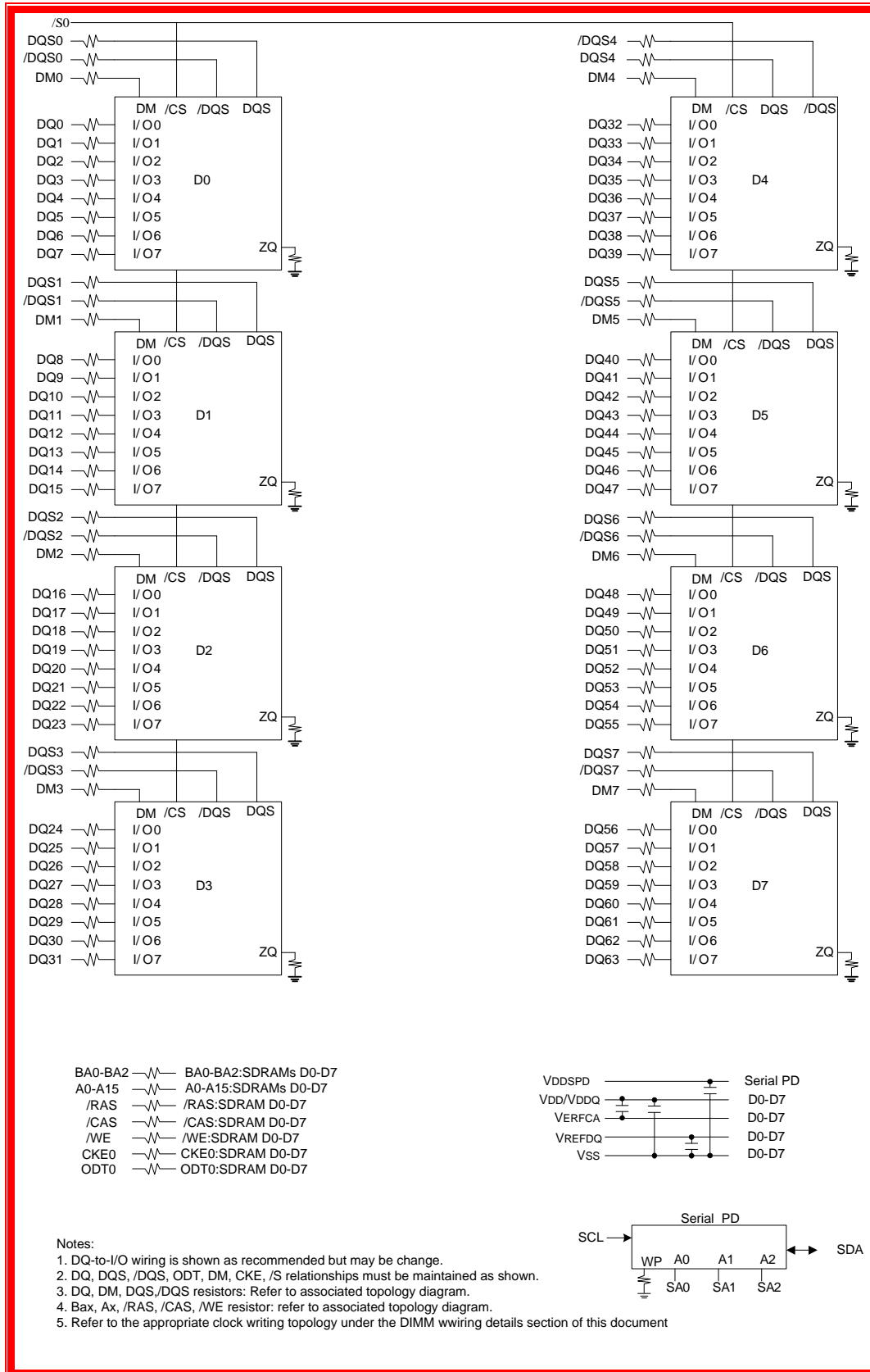
* NC = No Connect
 ** TEST (PIN# 125) reserve for bus probing, is NC on normal modules.
 *** Pin might connected to NC ball od DRAMs (depending on density); alternatively may connect to termination resistor

6. Architecture

Pin Definition

Pin Name	Description	Pin Name	Description
A0 - A13 (A14 or A15)	SDRAM address bus	SCL	Serial Presence Detect Clock Input
BA0 - BA1 (or BA2)	SDRAM Bank Address Inputs	SDA	Serial Presence Detect Data input/output
/RAS	SDRAM row address strobe	SA0 – SA2	Serial Presence Detect Address Inputs
/CAS	SDRAM column address strobe	V _{DD}	Power Supply
/WE	SDRAM write enable	V _{DDID}	V _{DD} Identification Flag
/S0 - /S1	DIMM Rank Select Lines	V _{DDQ}	SDRAM I/O Driver power supply
CK0 – CKE1	SDRAM clock enable lines	V _{REFDQ}	SDRAM I/O Reference supply
DQ0 – DQ63	DIMM memory data bus	V _{REFCA}	SDRAM Command/address reference supply.
CB0 – CB7	DIMM ECC check bit	V _{SS}	Ground
DQS0 – DQS8 /DQS0-/DQS8	SDRAM data strobes	V _{DDSPD}	Serial EEPROM positive power supply
DM0 – DM8	SDRAM data masks	NC	Spare Pin
ODT0-ODT1	Spare Pin	/Reset	Reset enable
CK0 – CK1 /CK0 - /CK1	Differential SDRAM Clocks	Event#	Reserved for optional temperature-sensing hardware
RSVD	Reserved for future use.	V _{TT}	SDRAM I/O termination supply.

7. Function Block Diagram:
 - (2GB, 1 Rank, 256x64 DDR3 SDRAMs)



8. DRAM Absolute Maximum Ratings

Symbol	Parameter	Rating	Units	Note	
T _{OPER}	Operation Temperature	Normal Operating Temp.	0 to 85	°C	1,2
		Extended Temp.(optional)	85 to 95	°C	1,3
T _{STG}	Storage Temperature	-55 to 100	°C	4,5	
V _{IN} , V _{OUT}	Voltage on any pins relative to V _{ss}	-0.4 to +1.975	V	4	
V _{DD}	Voltage on VDD supply relative to V _{ss}	-0.4 to +1.975	V	4,6	
V _{DDQ}	Voltage on VDDQ supply relative to V _{ss}	-0.4 to +1.975	V	4,6	

Note:

1. Operating Temperature T_{OPER} is the case surface temperature on the center / top side of the DRAM.

For measurement conditions, please refer to the JEDEC document JESD51-2.

2. The Normal Temperature Range specifies the temperatures where all DRAM specifications will be supported. During operation, the DRAM case temperature must be maintained between 0 to 85 °C under all operating conditions.

3. Some applications require operation of the DRAM in the Extended Temperature Range between 85 °C and 95 °C case temperature. Full specifications are supported in this range, but the following additional conditions apply:

- a) Refresh commands must be doubled in frequency, therefore reducing the Refresh interval tREFI to 3.9 μs. It is also possible to specify a component with 1X refresh (tREFI to 7.8μs) in the Extended Temperature Range. Please refer to supplier data sheet and/or the DIMM SPD for option availability.
- b) If Self-Refresh operation is required in the Extended Temperature Range, then it is mandatory to either use the Manual Self-Refresh mode with Extended Temperature Range capability (MR2 A6 =0b and MR2 A7 = 1b) or enable the optional Auto Self-Refresh mode (MR2 A6 = 1b and MR2 A7 =0b). Please refer to the supplier data sheet and/or the DIMM SPD for Auto Self-Refresh option availability, Extended Temperature Range support and tREFI requirements in the Extended Temperature Range.

4. Stresses greater than those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is stress rating only, and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

5. Storage Temperature is the case surface temperature on the center/top side of the DRAM. For the measurement conditions, please refer to JESD51-2 standard.

6. VDD and VDDQ must be within 300 mV of each other at all times;and VREF must be not greater than 0.6 x VDDQ, When VDD and VDDQ are less than 500 mV; VREF may be equal to or less than 300 mV

9. DRAM AC & DC Operating

Symbol	Parameter	Min	Typ.	Max	Units	Notes
Recommended DC Operating Conditions						
V_{DD}	Supply Voltage	1.425	1.5	1.575	V	1,2
V_{DDQ}	Supply Voltage	1.425	1.5	1.575	V	1,2
Single Ended AC/DC Input Levels						
V_{IH} (DC)	DC Input High (Logic1) Voltage	$V_{REF} + 0.1$	-	V _{DD}	V	3
V_{IL} (DC)	DC Input Low (Logic 0) Voltage	V _{SS}	-	$V_{REF} - 0.1$	V	3
V_{IH} (AC)	AC Input High (Logic1) Voltage	$V_{REF} + 0.175$	-	-	V	3
V_{IL} (AC)	AC Input Low (Logic 0) Voltage	-	-	$V_{REF} - 0.175$	V	3
V_{REFDQ} (DC)	Reference Voltage for DQ, DM inputs	$0.49V_{DDQ}$	$0.5V_{DDQ}$	$0.51V_{DDQ}$	V	4,5
V_{REFCA} (DC)	Reference Voltage for ADD,CMD inputs	$0.49V_{DDQ}$	$0.5V_{DDQ}$	$0.51V_{DDQ}$	V	4,5
Single Ended AC/DC output Levels						
V_{OH} (DC)	DC output high measurement level (for IV curve linearity)	-	$0.8 \times V_{DDQ}$	-	V	
V_{OM} (DC)	DC output mid measurement level (for IV curve linearity)	-	$0.5 \times V_{DDQ}$	-	V	
V_{OL} (DC)	DC output low measurement level (for IV curve linearity)	-	$0.2 \times V_{DDQ}$	-	V	
V_{OH} (AC)	AC output high measurement level (for output SR)	-	$V_{TT} + 0.1 \times V_{DDQ}$	-	V	6
V_{OL} (AC)	AC output low measurement level (for output SR)	-	$V_{TT} - 0.1 \times V_{DDQ}$	-	V	6

Symbol	Parameter	Min	Typ.	Max	Units	Notes
Differential AC/DC Input Levels						
V_{IHdiff}	Differential Input high	+0.2	-	Note 9	V	7
V_{ILdiff}	Differential Input logic Low	Note 9	-	-0.2	V	7
V_{IHdiff(ac)}	Differential Input high ac	2* (V _{IH (AC)} - V _{REF})	-	Note 9	V	8
V_{ILdiff(ac)}	Differential Input logic Low ac	Note 9	-	2* (V _{REF} - V _{IL (AC)})	V	8
Differential AC and DC Output Levels						
V_{OHdiff(AC)}	AC differential output high measurement level (for output SR)	-	+ 0.2 x V _{DDQ}	-	V	10
V_{OLdiff(AC)}	AC differential output low measurement level (for output SR)	-	- 0.2 x V _{DDQ}	-	V	10
Note:						
<ol style="list-style-type: none"> Under all conditions V_{DDQ} must be less than or equal to V_{DD}. V_{DDQ} tracks with V_{DD}. AC parameters are measured with V_{DD} and V_{DDQ} tied together. For DQ and DM, V_{ref} = V_{refDQ}. For input only pins except RESET#, V_{ref} = V_{refCA}. The ac peak noise on V_{Ref} may not allow V_{Ref} to deviate from V_{Ref(DC)} by more than +/-1% V_{DD} (for reference: approx. +/- 15 mV). For reference: approx. V_{DD}/2 +/- 15 mV. The swing of ± 0.1 × V_{DDQ} is based on approximately 50% of the static single-ended output high or low swing with a driver impedance of 40 Ω and an effective test load of 25 Ω to V_{TT} = V_{DDQ}/2 Used to define a differential signal slew-rate. For CK - CK# use V_{IH}/V_{IL(ac)} of ADD/CMD and V_{REFCA}; for DQS - DQS#, DQSL, DQSL#, DQSU, DQSU# use V_{IH}/V_{IL(ac)} of DQs and V_{REFDQ}; if a reduced ac-high or ac-low level is used for a signal group, then the reduced level applies also here. These values are not defined, however the single-ended signals CK, CK#, DQS, DQS#, DQSL, DQSL#, DQSU, DQSU# need to be within the respective limits (V_{IH(dc)} max, V_{IL(dc)}min) for single- ended signals as well as the limitations for overshoot and undershoot. The swing of ± 0.2 × V_{DDQ} is based on approximately 50% of the static single-ended output high or low swing with a driver impedance of 40 Ω and an effective test load of 25 Ω to V_{TT} = V_{DDQ}/2 at each of the differential outputs. 						

10. Operating, Standby, and Refresh Currents

- 2GB SODIMM (1 Rank, 256Mx8 DDR3 SDRAMs $T_{CASE} = 0\text{ }^{\circ}\text{C} \sim 70\text{ }^{\circ}\text{C}$)

Symbol	Parameter/Condition		PC3-10600	Unit
I DD0	One bank; Active - Precharge		640	mA
I DD1	One bank; Active - Read - Precharge		720	mA
I DD2N	Precharge Standby Current		480	mA
IDD2NT	Precharge Standby ODT Current		560	mA
I DD2P	Precharge Power Down Current	Fast Mode	240	mA
	Precharge Power Down Current	Slow Mode	192	mA
I DD2Q	Precharge Quiet Standby Current		480	mA
I DD3N	Active Standby Current		560	mA
I DD3P	Active Power-Down Current		240	mA
I DD4R	Operating Current Burst Read		1000	mA
I DD4W	Operating Current Burst Write		1000	mA
I DD5B	Burst Refresh Current		1480	mA
I DD6	Self-Refresh Current: Normal Temperature Range		192	mA
I DD6ET	Self-Refresh Current: Extended Temperature Range		240	mA
I DD6TC	Auto Self-Refresh Current		240	mA
I DD7	Operating Bank Interleave Read Current		1320	mA

11. Timing Parameters

($T_{CASE} = 0\text{ }^{\circ}\text{C} \sim 70\text{ }^{\circ}\text{C}$; $V_{DDQ} = V_{DD}$, See AC Characteristics)

Symbol	Parameter	PC3-10600		Unit
		Min.	Max.	
Clock Timing				
tCK (DLL-Off)	Minimum Clock Cycle Time	8	-	ns
tCK (avg)	Average Clock Period	1.5	3.3	ns
tCH (avg)	Average high pulse width	0.47	0.53	tCK (avg)
tCL (avg)	Average low pulse width	0.47	0.53	tCK (avg)
tCK (abs)	Absolute Clock Period	tCK(avg) min + tJIT(per) min	tCK(avg) max + tJIT(per) max -	Ps
tCH (abs)	Absolute high pulse width	0.43	-	tCK (avg)
tCL (abs)	Absolute low pulse width	0.43	-	tCK (avg)
JIT (per)	Clock Period Jitter	-80	80	Ps
TJIT (per, lck)	Clock Period Jitter during DLL locking period.	-70	70	Ps
JIT (CC)	Cycle to Cycle Period Jitter	160		Ps
TJIT (CC, lck)	Cycle to Cycle Period Jitter during DLL locking period.	140		Ps
TJIT (duty)		-	-	Ps
TERR (2per)	Cumulative error across 2 cycle	-118	118	Ps
TERR (3per)	Cumulative error across 3 cycle	-140	140	Ps
TERR (4per)	Cumulative error across 4 cycle	-155	155	Ps
TERR (5per)	Cumulative error across 5 cycle	-168	168	Ps
TERR (6per)	Cumulative error across 6 cycle	-177	177	Ps
TERR (7per)	Cumulative error across 7 cycle	-186	186	Ps
TERR (8per)	Cumulative error across 3 cycle	-193	193	Ps
TERR (9per)	Cumulative error across 4 cycle	-200	200	Ps
TERR (10per)	Cumulative error across 5 cycle	-205	205	Ps

TERR (11per)	Cumulative error across 6 cycle	-210	210	Ps
TERR (12per)	Cumulative error across 7 cycle	-215	215	Ps
TERR (nper)	Cumulative error across 13~50 cycle	$tERR(nper)min = (1 + 0.68ln(n)) *$ $tJIT(per)min$ $tERR(nper)max = (1 + 0.68ln(n)) *$ $tJIT(per)max$		Ps
Data Timing				
Symbol	Parameter	Min.	Max.	Unit
tDSQ	DQS, DQS# to DQ skew, per group, per access	-	125	Ps
tQH	DQ output hold time from DQS, DQS#	0.38	-	tCK(avg)
tLZ (DQ)	DQ low-impedance time from CK, CK#	-500	250	Ps
tHZ(DQ)	DQ high impedance time from CK, CK#	-	250	Ps
tDS(base) AC150	Data setup time to DQS, DQS# referenced to Vih(ac) / Vil(ac) levels	30	-	Ps
tDH(base) DC 100	Data hold time from DQS, DQS# referenced to Vih(dc) / Vil(dc) levels	65	-	Ps
Data Strobe Timing				
Symbol	Parameter	Min.	Max.	Unit
tRPRE	DQS,DQS# differential READ Preamble	0.9		tCK(avg)
tRPST	DQS, DQS# differential READ Postamble	0.3		tCK(avg)
tQSH	DQS, DQS# differential output high time	0.4		tCK(avg)
tQSL	DQS, DQS# differential output low time	0.4		tCK(avg)
tWPRE	DQS, DQS# differential WRITE Preamble	0.9		tCK(avg)
tWPST	DQS, DQS# differential WRITE Postamble	0.3		tCK(avg)
tDQSK	DQS, DQS# rising edge output access time from rising CK, CK#	-225	225	Ps

tLZ(DQS)	DQS and DQS# low-impedance time (Referenced from RL - 1)	-450	225	Ps
tHZ(DQS)	DQS and DQS# high-impedance time (Referenced from RL + BL/2)	-	225	Ps
tDQSL	DQS, DQS# differential input low pulse width	0.4	0.6	tCK(avg)
tDQSH	DQS, DQS# differential input high pulse width	0.4	0.6	tCK(avg)
tDQSS	DQS, DQS# rising edge to CK, CK# rising edge	-0.25	0.25	tCK(avg)
tDSS	DQS, DQS# falling edge setup time to CK, CK# rising edge	0.2	-	tCK(avg)
tDSH	DQS, DQS# falling edge hold time from CK, CK# rising edge	0.2	-	tCK(avg)
Command and Address Timing				
Symbol	Parameter	Min.	Max.	Unit
tDLLK	DLL locking time	512	-	nCK
tRTP	Internal READ Command to PRECHARGE Command delay	max(4nCK, 7.5ns)	-	
tWTR	Delay from start of internal write transaction to Internal read command	max(4nCK, 7.5ns)	-	
tWR	WRITE recovery time	15	-	ns
tMRD	Mode Register Set command cycle time	4	-	nCK
tMOD	Mode Register Set command update delay	max(12nCK, 15ns)	-	
tRCD	Refer to Section 1 Feature			
tRP	Refer to Section 1 Feature			
tRC	Refer to Section 1 Feature			
tCCD		4	-	nCK

tDAL (min)	Auto precharge write recovery + precharge time	WR + roundup(tRP / tCK(avg))		nCK
tMPRR	Multi-Purpose Register Recovery Time	1	-	nCK
tRAS	ACTIVE to PRECHARGE command period	36	9 tREFI	ns
tRRD	ACTIVE to ACTIVE command period for 1KB page size	max(4nCK, 6ns)	-	
tRRD	ACTIVE to ACTIVE command period for 2KB page size	max(4nCK, 7.5ns)	-	
tFAW	Four activate window for 1KB page size	30	-	ns
tFAW	Four activate window for 2KB page size	45	-	ns
tIS (base)	Command and Address setup time to CK, CK#, referenced to Vih(ac) / Vil(ac) levels.	65		ns
tIH(base)	Command and Address hold time from CK, CK# referenced to Vih(dc) / Vil(dc) levels	140		ps
tIS(base) AC150	Command and Address setup time to CK, CK# referenced to Vih(ac) / Vil(ac) levels	65+125		ps
Calibration Timing				
Symbol	Parameter	Min.	Max.	Unit
tZQinit	Power-up and RESET calibration time	512	-	nCK
tZQoper	Normal operation Full calibration time	256	-	nCK
tZQCS	Normal operation Short calibration time	64	-	nCK
Reset Timing				
Symbol	Parameter	Min.	Max.	Unit
tXPR	Exit Reset from CKE HIGH to a valid command	max(5nCK, tRFC(min) + 10ns)	-	
Self Refresh Timings				

Symbol	Parameter	Min.	Max.	Unit
tXS	Exit Self Refresh to commands not requiring a locked DLL	Max(5nCK), tRFC(min) +10ns)		
tXSDLL	Exit Self Refresh to commands requiring a locked DLL.	tDLL(min)	-	nCK
tCKESR	Minimum CKE low width for Self Refresh entry to exit timing.	tCKE9min) +1nCK	-	
tCKSRE	Valid Clock Requirement after Self Refresh Entry (SRE) or Power-Down Entry (PDE)	Max(5nCK, ,10ns)	-	
tCKSRX	Valid Clock Requirement before Self Refresh Exit (SRX) or Power-Down Exit (PDX) or Reset Exit	Max(5nCK, ,10ns)	-	
Power Down Timings				
Symbol	Parameter	Min.	Max.	Unit
tXP	Exit Power Down with DLL on to any valid command; Exit Precharge Power Down with DLL frozen to commands not requiring a locked DLL	max(3nCK, 6ns)	-	
tXPDLL	Exit Precharge Power Down with DLL frozen to commands requiring a locked DLL	max(10nCK, 24ns)	-	
tCKE	CKE minimum pulse width	max(3nCK, 5.625ns)	-	
tCPDED	Command pass disable delay	1	-	nCK
tPD	Power Down Entry to Exit Timing	tCK(min)	9*tREFI	
tACTPDEN	Timing of ACT command to Power Down entry	1	-	nCK
tPRPDEN	Timing of PRE or PREA command to Power Down entry	1	-	nCK

tRDPDEN	Timing of RD/RDA command to Power Down entry	RL+4+1	-	nCK
tWRPDEN	Timing of WR command to Power Down entry (BL8OTF, BL8MRS, BC4OTF)	WL + 4 + (tWR / tCK(avg))	-	nCK
tWRAPDEN	Timing of WRA command to Power Down entry (BL8OTF, BL8MRS, BC4OTF)	WL + 4 + WR + 1	-	nCK
tWRPDEN	Timing of WR command to Power Down entry (BC4MRS)	WL + 2 + (tWR / tCK(avg))	-	nCK
tWRAPDEN	Timing of WRA command to Power Down entry (BC4MRS)	WL + 2 + WR + 1	-	nCK
tREFPDEN	Timing of REF command to Power Down entry	1	-	nCK
tMRSPDEN	Timing of MRS command to Power Down entry	tMOD(mi n)	-	nCK
ODT Timings				
Symbol	Parameter	Min.	Max.	Unit
ODTH4	ODT high time without write command or with write command and BC4	4	-	nCK
ODTH8	ODT high time with Write command and BL8	6	-	nCK
tAONPD	Asynchronous RTT turn-on delay (Power-Down with DLL frozen)	1	9	ns
tAOFPD	Asynchronous RTT turn-off delay (Power-Down with DLL frozen)	1	9	ns
tAON	RTT-turn-on	-250	250	ps
tAOF	RTT_Nom and RTT_WR turn-off time from ODTLoff reference	0.3	0.7	tCK(avg)
tADC	RTT dynamic change skew	0.30.7		tCK(avg)

Write Leveling Timing				
Symbol	Parameter	Min.	Max.	Unit
tWLMRD	First DQS/DQS# rising edge after write leveling mode is programmed	40	-	nCK
tWLDQSEN	DQS/DQS# delay after write leveling mode is programmed	25	-	nCK
tWLS	Write leveling setup time from rising CK, CK# crossing to rising DQS, DQS# crossing	195	-	ps
tWLH	Write leveling hold time from rising DQS, DQS# crossing to rising CK, CK# crossing	195	-	ps
tWLO	Write leveling output delay	0	9	ns
tWLOE	Write leveling output error	0	2	ns

12. SPD Serial Presence Detect – (2GB)

1 RANK UNBUFFERED DDR SDRAM DIMM based on 256Mx8, 8Banks, 8K Refresh, DDR3 SDRAMs with SPD

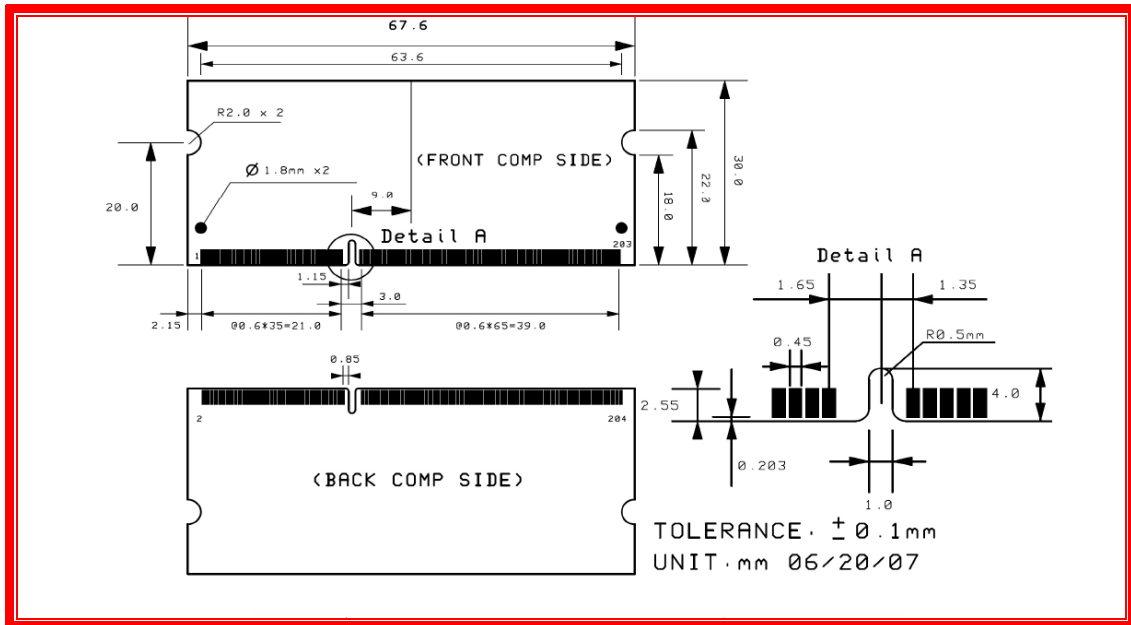
Byte	Description	Serial PD Data Entry (Hexadecimal)	Note
0	Number of Serial PD Bytes Written during Production	92	
1	SPD Revision	10	
2	Key Byte/DRAM Device Type	0B	
3	Key Byte/Module type	03	
4	SDRAM Density and Banks	03	
5	SDRAM Address	19	
6	Reserve	00	
7	Module Organization	01	
8	Module Memory Bus Width	03	
9	Fine Timebase (FTB) Dividend/Divisor	52	
10	Medium Timebase (MTB) Dividend	01	
11	Medium Timebase (MTB) Divisor	08	
12	SDRAM Minimum Cycle Time (tCKmin)	0C	
13	Reserve	00	
14	CAS latency, least Significant Byte	3C	
15	CAS latency, most Significant Byte	00	
16	Minimum CAS Latency Time (tAAmin)	69	
17	Minimum Write Recovery Time (tWRmin)	78	

Byte	Description	Serial PD Data Entry (Hexadecimal)	Note
18	Minimum RAS# to CAS# Delay Time (tRCDmin)	69	
19	Minimum Row Active to Row Active Delay Time (tRRDmin)	30	
20	Minimum Row Precharge Delay Time (tRPmin)	69	
21	Upper Nibbles for tRAS and tRC	11	
22	Minimum Active to Precharge Delay Time (tRASmin), Least Significant Byte	20	
23	Minimum Active to Active/Refresh Delay Time (tRCmin), Least Significant Byte	89	
24	Minimum Refresh Recovery Delay Time (tRFCmin), Least Significant Byte	00	
25	Minimum Refresh Recovery Delay Time (tRFCmin), Most Significant Byte	05	
26	Minimum Internal Write to Read Command Delay Time (tWTRmin)	3C	
27	Minimum Internal Read to Precharge Command Delay Time (tRTPmin)	3C	
28	Upper Nibble for tFAW	00	
29	Minimum Four Activate Window Delay Time (tFAWmin)	F0	
30	SDRAM Optional Features	83	
31	SDRAM Thermal and Refresh Options	05	
32	Module Thermal Sensor	00	
33	SDRAM Device Type	00	

34-59	Reserve	00	
60-63	Module Type Specific Section,	0F 11 01 00	
64-117	Reserve	00	
117-118	Module ID: Module Manufacturer's JEDEC ID Code	86 F1	
119	Module ID: Module Manufacturing Location	02	
120-121	Module ID: Module Manufacturing Date	0A 03	
122-255	reserve	-	

13. PACKAGE DIMENSION

- (2GB, 2 Ranks, 256Mx8 DDR base SODIMM)



Note: Device position is only for reference.

14. RoHS Declaration



Declaration of Conformity

We, InnoDisk Co., Ltd, here declare the product M3SW-2GSJCCN9/-(X) complies with the requirement of RoHS directives 2011/65/EU and 2006/12/EC.

Innodisk ensures the above product meets RoHS requirements of six restricted substances. This declaration is based on vendor supplied analysis/MSDS, material certifications, and/ or 3rd party test reports of the component/ raw materials used in the manufacture of products.

Name of hazardous substance	Limited of RoHS ppm (mg/kg)
Cd	< 100 ppm
Pb	< 1000 ppm
Hg	< 1000 ppm
Chromium VI (Cr+6)	< 1000 ppm
Polybromodiphenyl ether (PBDE)	< 1000 ppm
Polybrominated Biphenyls (PBB)	< 1000 ppm
Perfluorooctane Sulfonate (PFOS)	Not Contained

Date issued: 2013/01/22

Manufacturer: : InnoDisk Co., Ltd.
 Address : 9F, No. 100, Sec.1 Xintai 5th Rd.,
Xizhi City, Taipei 221, Taiwan

Authorized Signature :

QA Dept. Director – Ryan Tsai

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Revision Log

Rev	Date	Modification
0.1	19 th December 2013	Preliminary Edition
1.0	19 th December 2013	Official released.